

## Supporting Information

### **An anisotropically crystallized and nitrogen-doped CuWO<sub>4</sub> photoanode for efficient and robust visible-light-driven water oxidation**

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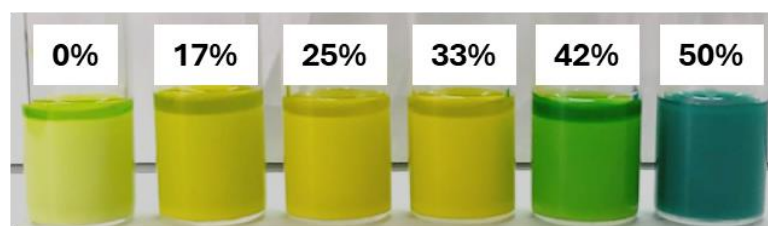
**Figure S9.** DRS of the N-CuWO<sub>4</sub> film before and after photoelectrolysis.

**Table S1.** Comparison of performances of state-of-the-art CuWO<sub>4</sub>-based photoanodes for PEC water oxidation.<sup>a)</sup>

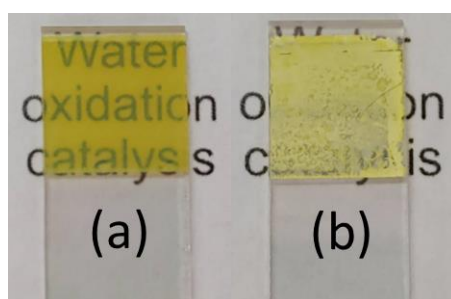
Sample	Synthesis	Buffer	pH	$j_{1.23}$ / mA cm <sup>-2</sup>	IPCE <sub>420</sub> (%)	$\eta_{\text{sep}}$ (%)	$\eta_{\text{cat}}$ (%)	FE <sub>O<sub>2</sub></sub> (%)	Stability: Remaining photocurrent (%) (reaction time)	Ref.
N-CuWO <sub>4</sub>	MiMIC	0.1 M KPi	7.0	0.21	5.6	12.3 <sup>b)</sup>	51.9 <sup>b)</sup>	97 <sup>c)</sup>	92 (40 h) <sup>c)</sup>	This work
CuWO <sub>4</sub> nanoflake	Sacrificial templates	1.0 M KBi	9.5	0.4	8	12	55	nr	100 (5 h)	R1
CuWO <sub>4</sub> nanoflake	Sacrificial templates	0.1 M KPi	7.0	0.3	nr	nr	nr	nr	95 (1 h)	R2
CuWO <sub>4</sub> nanoflake	Sacrificial templates	0.2 M Na <sub>2</sub> SO <sub>4</sub>	7.0	0.09	nr	10.8	15.8	nr	45 (6 h)	R3
CuWO <sub>4</sub> with oxygen vacancy	Sacrificial templates	0.2 M Na <sub>2</sub> SO <sub>4</sub>	7.0	0.2	nr	11.2	26.2	nr	60 (6 h)	R3
CuWO <sub>4</sub>	Ultrasonic spray pyrolysis	0.2 M Na <sub>2</sub> SO <sub>4</sub>	6.4	0.033	nr	nr	nr	nr	96 (2100 s)	R4
CuWO <sub>4</sub> on carbon nanotube	Spray pyrolysis	0.25 M (NaHCO <sub>3</sub> /Na <sub>2</sub> CO <sub>3</sub> )	10.0	0.23	7 <sup>d)</sup>	nr	nr	nr	85 (24 h) <sup>d)</sup>	R5
CuWO <sub>4</sub>	Spray pyrolysis	0.1 M KPi	7.0	0.13	< 1	2.5	25	nr	nr	R6
CuWO <sub>4</sub>	Spray pyrolysis	0.1 M KBi	7.0	0.08	nr	nr	nr	nr	nr	R7
CuWO <sub>4</sub>	Spin-coating	0.5 M KBi with 0.2M KCl	7.0	0.1	nr	nr	nr	nr	nr	R8
CuWO <sub>4</sub>	Spin-coating	0.1 M KPi	7.0	0.15	nr	nr	nr	100	15 (12 h)	R9
CuWO <sub>4</sub>	Spin-coating	0.1 M KBi	7.0	0.10	nr	nr	nr	96	93 (12 h)	R9
CuWO <sub>4</sub>	Spin-coating	0.1 M Na <sub>2</sub> SO <sub>4</sub>	6.8	0.267	2	nr	nr	nr	nr	R10
Nodular CuWO <sub>4</sub>	Electrochemical deposition	0.1 M KPi	7.0	0.072	21 <sup>e)</sup>	nr	nr	> 90	nr	R11

CuWO <sub>4</sub>	Electrochemical deposition	0.1 M KPi	7.0	0.026	0.2	nr	nr	nr	81 (150 s)	R12
CuWO <sub>4</sub> nanoparticle	Spray pyrolysis	0.1 M KPi	7.0	0.03	2	nr	nr	nr	50 (4000 s)	R13
CuWO <sub>4</sub>	Spray pyrolysis	0.3 M KBi	7.5	0.027	0.03	nr	nr	nr	nr	R14
N <sub>2</sub> -treated CuWO <sub>4</sub>	Electrochemical deposition	0.1 M KPi	7.0	0.08	nr	4	nr	nr	nr	R15
H <sub>2</sub> -treated CuWO <sub>4</sub>	Hydrothermal	0.1 M Na <sub>2</sub> SO <sub>4</sub>	6.8	0.2	nr	nr	nr	nr	75 (1 h) <sup>e)</sup>	R16
CuWO <sub>4</sub> nanoparticle	Electrochemical deposition	0.1 M KPi	7.0	0.015	0.2	1.5	23	nr	nr	R17
Porous CuWO <sub>4</sub>	Electrochemical deposition	0.1 M KPi	7.0	0.2	nr	nr	nr	nr	~80 (12 h) <sup>d)</sup>	R18
CuWO <sub>4</sub> with a predominant (100) facet	Hydrothermal	0.2 M KPi	~7	0.38	11	20.4	26.2	75	85 (6 h)	R19
Polycrystalline CuWO <sub>4</sub>	RF magnetron sputtering	0.33 M H <sub>3</sub> PO <sub>4</sub>	1.35	0.126	nr	nr	nr	nr	nr	R20
CuWO <sub>4</sub>	Spray pyrolysis	0.1 M KPi	7.0	0.5	nr	nr	nr	nr	~80 (10 h)	R21

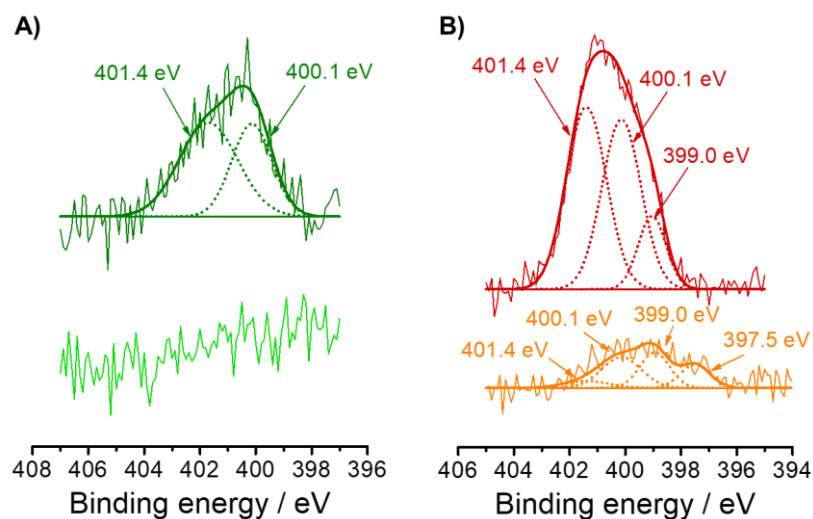
<sup>a)</sup> nr: not reported, measured at 1.23V vs. RHE with simulated solar light (AM 1.5, 100 mW cm<sup>-2</sup>), <sup>b)</sup> monoclinic light (LED, 420 nm, 3.78 mW cm<sup>-2</sup>), <sup>c)</sup> visible light (Xe lamp with L39 and heat-cut filter, 100 mW cm<sup>-2</sup>), <sup>d)</sup> at 1.63 V vs. RHE, <sup>e)</sup> at 1.6 V vs. RHE, <sup>f)</sup> at 1.1 V vs. RHE.



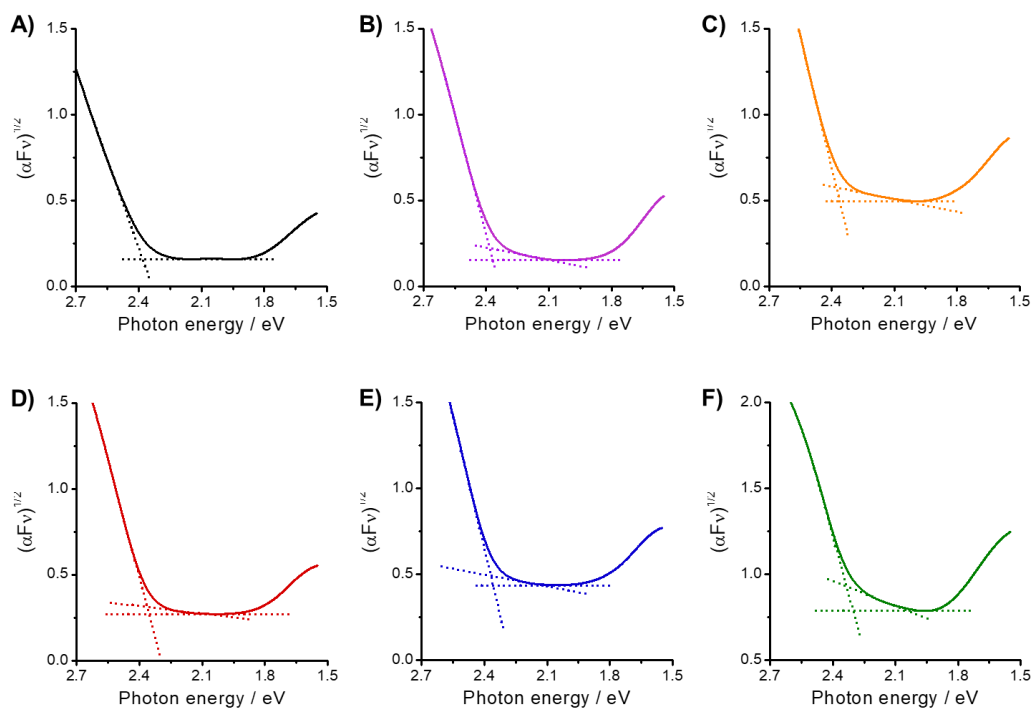
**Figure S1** Photos of precursor suspensions containing 0.42 M  $\text{Cu}(\text{NO}_3)_2$  and 0.50 M  $\text{WCl}_6$  with different fractions ( $F_{\text{im}} = 0 \sim 50\%$  vol) of BIm in methanol/BIm mixed solvents.  $F_{\text{im}}$  values are indicated on the figure.



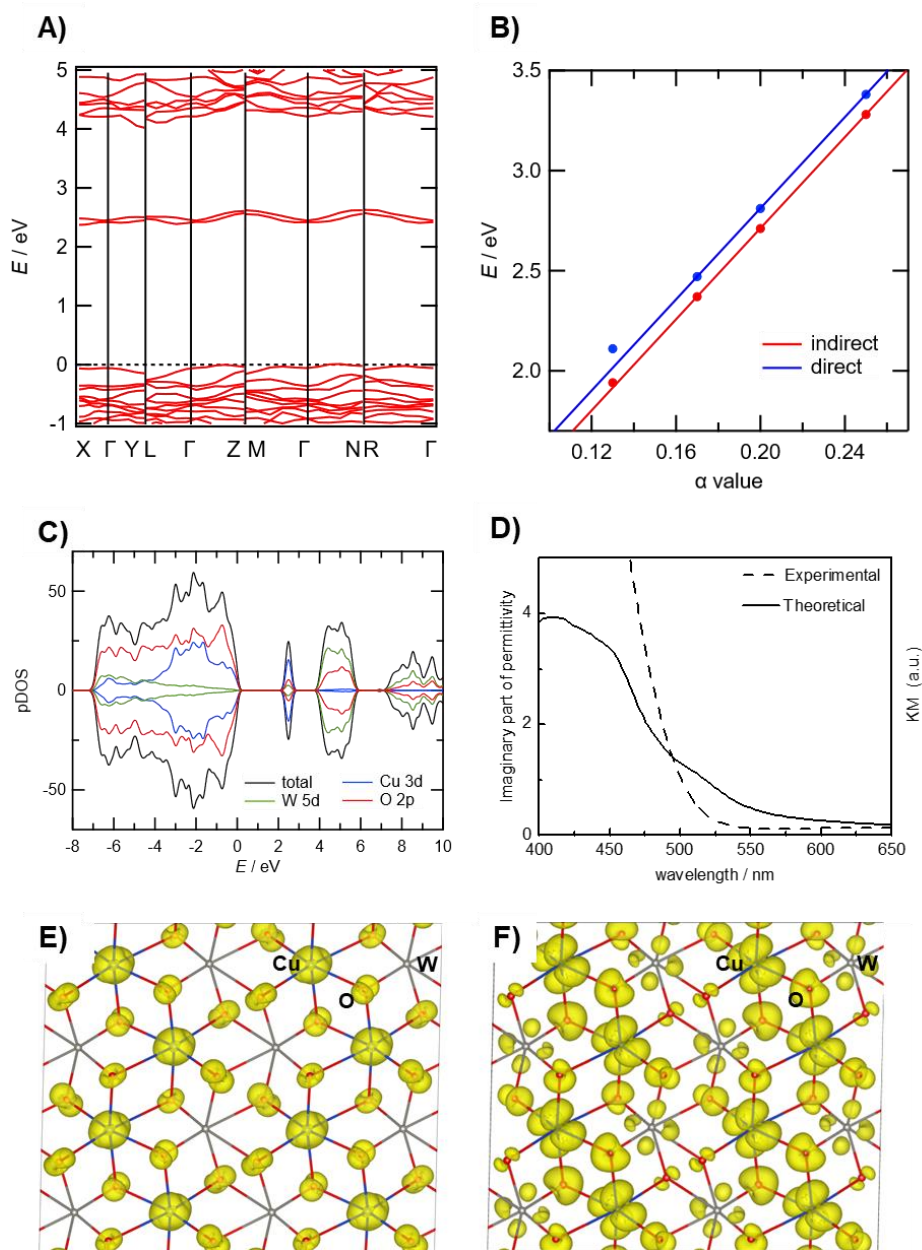
**Figure S2** Photos of  $\text{CuWO}_4$  films with  $F_{\text{im}}$  of (a) 33% and (b) 0% on an FTO substrate.



**Figure S3.** XPS spectra in the N1s region for  $\text{CuWO}_4$  films with  $F_{\text{im}}$  of (A) 0% and (B) 33% before (top) and after (bottom) a surface treatment with Ar plasma etching.



**Figure S4** Tauc plots based on the DRS spectra (Figure 4A) of  $\text{CuWO}_4$  films with  $F_{im}$  of (A) 0%, (B) 17%, (C) 25%, (D) 33%, (E) 42% and (F) 50%. The dotted lines represent slopes to calculate bandgap energies.



**Figure S5** (A) Band diagram calculated for neat  $\text{CuWO}_4$  crystals using HSE06 functional with the exact exchange mixing coefficient ( $\alpha$ ) of 0.17. (B) Plots of the calculated band gap versus  $\alpha$  values. (C) pDOS diagram (black) calculated for neat  $\text{CuWO}_4$  at  $\alpha = 0.17$ . Contributions from the Cu 3d (blue), O 2p (red) and W 5d (green) bands are indicated by different colors. (D) Imaginary part of the calculated dielectric coefficients (solid line) and the measured DRS spectrum for neat- $\text{CuWO}_4$  (dashed line). Integrated density of states (IDOS) of (E) the valence band (VB) top and (F) the conduction band (CB) bottom for neat  $\text{CuWO}_4$ . The atoms of Cu, O, and W are marked in figures.

**Table S2.** Parameters for calculation of replacement energies ( $E_{\text{rep}}(\Delta\epsilon_{\text{F}})$ ) of O1-O4 with  $\text{N}^{1-}$ ,  $\text{N}^{2-}$ , and  $\text{N}^{3-}$  for  $\text{CuWO}_4$ .

dopant	site	$q$	$E_{\text{rep}}(0)$
$\text{N}^{1-}$	O1	+1	3.59
	O2	+1	3.83
	O3	+1	3.82
	O4	+1	3.69
$\text{N}^{2-}$	O1	0	4.26
	O2	0	4.83
	O3	0	4.67
	O4	0	4.38
$\text{N}^{3-}$	O1	-1	4.93
	O2	-1	5.35
	O3	-1	5.05
	O4	-1	5.18

**Table S3.** Summary of energy levels of VB top and CB bottom, impurity bands, and transition energies estimated from the PDOS diagrams. <sup>a</sup>

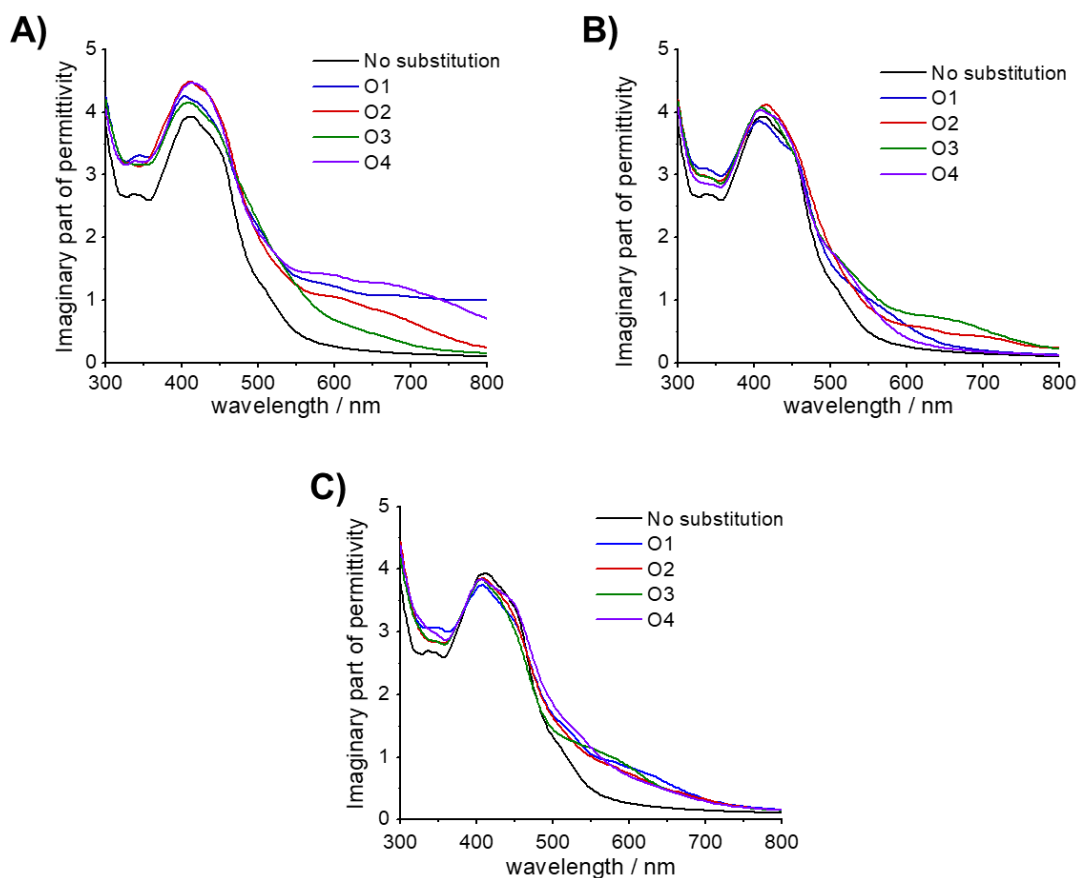
Dopant	Site	Spin	$E_{VB}$ / eV	$E_{N-d}$ / eV	$E_{N-a}$ / eV	$E_{CB}$ / eV	Transition energy / eV (Assignment)	
Neat		up	-0.42			1.95	2.37 (VB → CB)	
		down	-0.42			1.95	2.37 (VB → CB)	
N <sup>1-</sup>	O1	up	0.00			2.25	2.25 (VB → CB)	
			0.00		1.32		1.32 (VB → N-a1)	
		down	0.00			2.33	2.33 (VB → CB)	
			0.00		2.14		2.14 (VB → N-a2)	
	O2	up	0.00			2.23	2.23 (VB → CB)	
			0.00			2.31	2.31 (VB → CB)	
		down	0.00		1.97		1.97 (VB → N-a1)	
			0.00		1.67		1.67 (VB → N-a2)	
	O3	up	-0.14			2.10	2.24 (VB → CB)	
					-0.03		2.10	2.13 (N-d1 → CB)
		down	-0.09			2.22	2.19 (VB → CB)	
			-0.09		1.71		1.80 (VB → N-a1)	
O4	up	0.00			2.34	2.34 (VB → CB)		
		0.00		2.21		2.21 (VB → N-a1)		
	down	0.00		1.41		1.41 (VB → N-a2)		
		0.00			2.32	2.32 (VB → CB)		
N <sup>2-</sup>	O1	up	-0.29			2.00	2.30 (VB → CB)	
					-0.01		2.02	2.02 (N-d1 → CB)
		down	-0.33			2.02	2.36 (VB → CB)	
					-0.21		2.02	2.24 (N-d1 → CB)
	O2	up	-0.33			1.86	2.19 (VB → N-a1)	
		down	-0.57			1.71	2.28 (VB → CB)	
					-0.45		1.71	2.16 (N-d1 → CB)
	O3	up	-0.57			1.68	2.25 (VB → CB)	
					1.38		1.95 (VB → N-a1)	
		down	-0.57		-0.10		1.68	1.78 (N-d1 → CB)
					0.00		1.68	1.68 (N-d2 → CB)
O4	up	-0.10			1.38	1.48 (N-d1 → N-a1)		
				0.00	1.38		1.38 (N-d2 → N-a2)	
	down	-0.42			1.85	2.27 (VB → CB)		
				-0.28		1.85	2.16 (N-d1 → CB)	
O5	up	-0.44			1.85	2.29 (VB → CB)		
				-0.01		1.85	1.86 (N-d1 → CB)	
	down	-0.44		1.19		1.63 (VB → N-a1)		
				-0.01	1.19		1.20 (N-d1 → N-a1)	
O6	up	-0.20			2.12	2.32 (VB → CB)		
	down	-0.15		-0.02	2.12	2.14 (N-d1 → CB)		
					2.10	2.25 (VB → CB)		



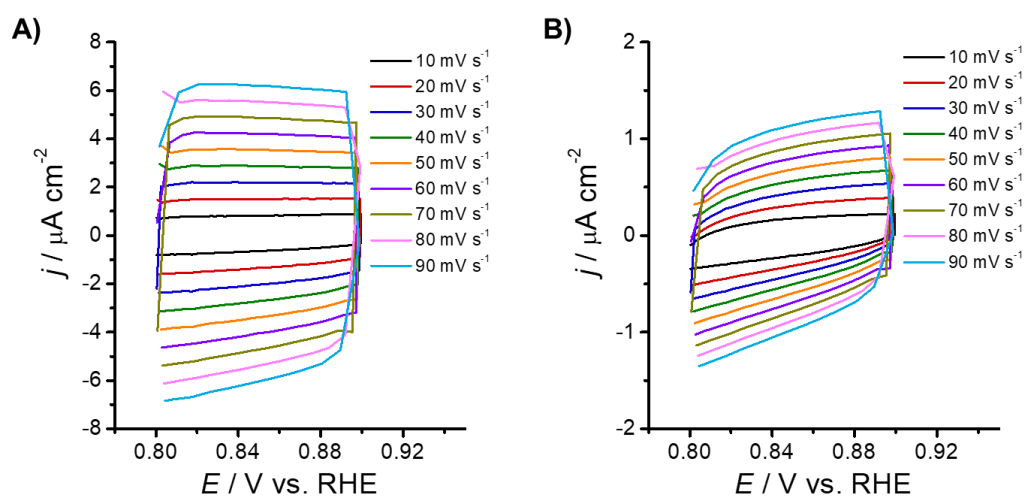
**Table S3. (continued)**

Dopant	Site	Spin	$E_{VB}$	$E_{N-d}$	$E_{N-a}$	$E_{CB}$	Transition energy (assignment)		
N <sup>3-</sup>	O1	up	-0.59			1.73	2.32 (VB → CB)		
					-0.43		1.73	2.16 (N-d1 → CB)	
					-0.20		1.73	1.93 (N-d2 → CB)	
		down			-0.09		1.73	1.82 (N-d3 → CB)	
						-0.59		1.73	2.32 (VB → CB)
						-0.44		1.73	2.17 (N-d1 → CB)
	O2	up	-0.53				1.73	1.74 (N-d2 → CB)	
					-0.31		1.79	2.32 (VB → CB)	
					-0.14		1.79	2.10 (N-d1 → CB)	
		down			-0.50		1.74	1.93 (N-d2 → CB)	
						-0.18		1.74	2.24 (VB → CB)
						-0.08		1.74	1.92 (N-d1 → CB)
O3	up	-0.58				1.74	1.82 (N-d2 → CB)		
				-0.40		1.74	1.75 (N-d3 → CB)		
				-0.31		1.74	2.33 (VB → CB)		
	down			-0.53		1.74	2.05 (N-d2 → CB)		
					-0.19		1.74	1.93 (N-d3 → CB)	
					-0.18		1.74	2.28 (VB → CB)	
O4	up	-0.52				1.74	1.92 (N-d1 → CB)		
				-0.32		1.74	1.75 (N-d2 → CB)		
				-0.09		1.74	2.05 (N-d1 → CB)		
	down			-0.50		1.73	1.83 (N-d2 → CB)		
					-0.01		1.73	2.24 (VB → CB)	
						1.73	1.73 (N-d1 → CB)		

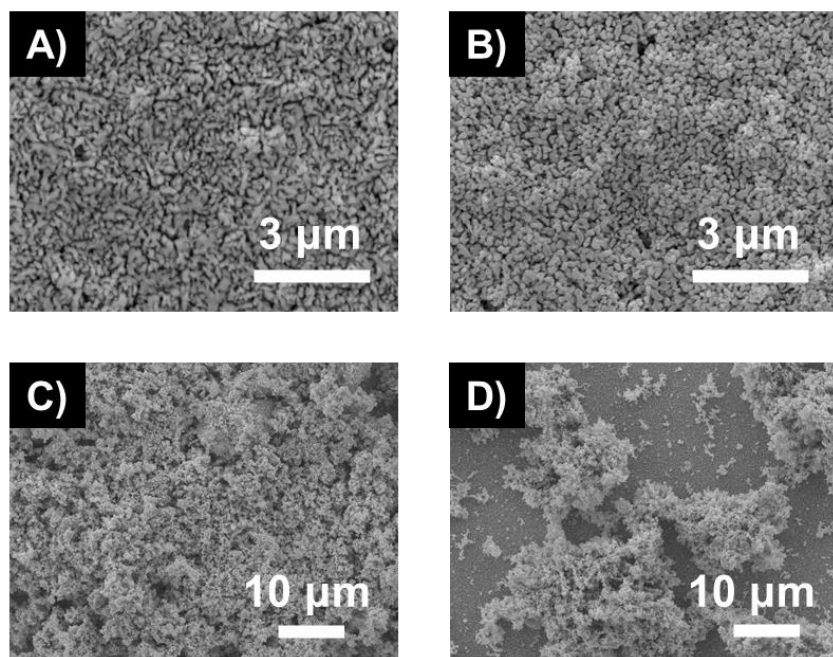
<sup>a)</sup>  $E_{VB}$ ,  $E_{VB}$ ,  $E_{N-d}$  and  $E_{N-a}$  are energy levels of VB top, CB bottom, donor and acceptor impurity bands due to N 2p orbitals, respectively.



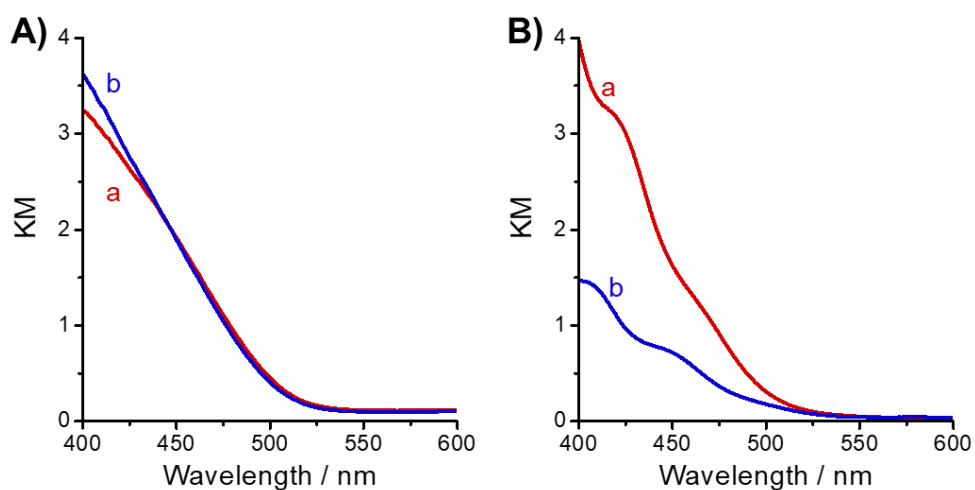
**Figure S6.** Imaginary part of the calculated dielectric coefficients for neat-CuWO<sub>4</sub> (black) and N-CuWO<sub>4</sub> with substitutions of O1-O4 with (A) N<sup>1-</sup>, (B) N<sup>2-</sup>, and (C) N<sup>3-</sup>. The replaced O atoms in O1-O4 are indicated by different colors in each figure.



**Figure S7** CVs of (A) N-CuWO<sub>4</sub> ( $F_{\text{im}} = 33\%$ ) and (B) neat-CuWO<sub>4</sub> electrodes as measured in 0.1 M KPi solutions (pH = 7) in the potential range of 0.8 – 0.9 V vs. RHE at different scan rates of 10 – 90 mV s<sup>-1</sup> under dark conditions.



**Figure S8** Top view SEM images of (A and B) N-CuWO<sub>4</sub> ( $F_{im} = 33\%$ ) and (C and D) neat-CuWO<sub>4</sub> electrode (A and C) before and (B and D) after 15 h photoelectrolysis in a 0.1 M KPi buffer (pH 7.0) at 1.23 V under the light irradiation (>390 nm, 100 mW cm<sup>-2</sup>).



**Figure S9** DRS of (A) N-CuWO<sub>4</sub> ( $F_{im} = 33\%$ ) and (B) neat-CuWO<sub>4</sub> electrodes before (a, red) and after 15 h photoelectrolysis (b, blue) in a 0.1 M KPi buffer (pH 7.0) at 1.23 V under the light irradiation (>390 nm, 100 mW cm<sup>-2</sup>).

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